

Automotive-grade N-channel 60 V, 4.4 mΩ typ., 80 A STripFET™ F6 Power MOSFET in a DPAK package

Datasheet - production data

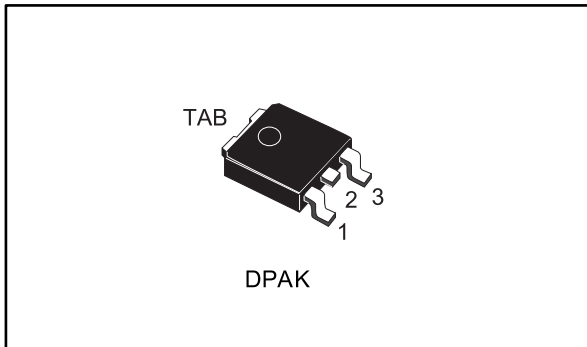
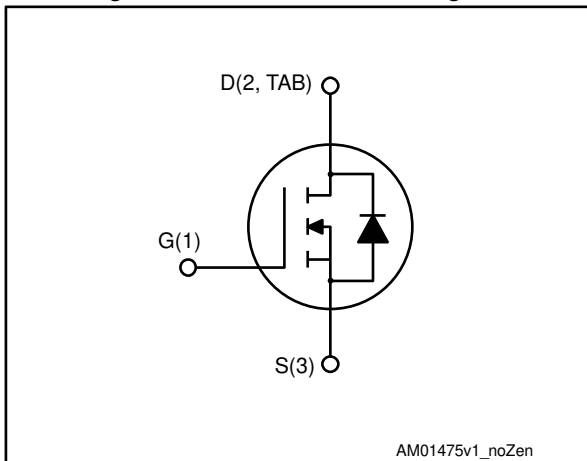


Figure 1: Internal schematic diagram



AM01475v1_noZen

Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STD80N6F6	60 V	5 mΩ	80 A

- AEC-Q101 qualified
- Very low on-resistance
- Very low gate charge
- High avalanche ruggedness
- Low gate drive power loss



Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the STripFET™ F6 technology with a new trench gate structure. The resulting Power MOSFET exhibits very low R_{DS(on)} in all packages.

Table 1: Device summary

Order code	Marking	Package	Packaging
STD80N6F6	80N6F6	DPAK	Tape and reel

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	60	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	80	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	80	A
$I_{DM}^{(2)}$	Drain current (pulsed)	320	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	120	W
T_{stg}	Storage temperature range	- 55 to 175	$^\circ\text{C}$
T_j	Operating junction temperature range		

Notes:

⁽¹⁾Current limited by package.

⁽²⁾ Pulse width limited by safe operating area.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	1.25	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	50	$^\circ\text{C}/\text{W}$

Notes:

⁽¹⁾When mounted on a 1-inch² FR-4 board, 2oz Cu.

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified).

Table 4: Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	60			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 60\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 60\text{ V}$, $T_j = 125\text{ °C}$ ⁽¹⁾			100	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3		4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 40\text{ A}$		4.4	5	m Ω

Notes:

⁽¹⁾Defined by design, not subject to production test.

Table 5: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	8325	-	pF
C_{oss}	Output capacitance		-	500	-	pF
C_{rss}	Reverse transfer capacitance		-	400	-	pF
Q_g	Total gate charge	$V_{DD} = 30\text{ V}$, $I_D = 80\text{ A}$, $V_{GS} = 0$ to 10 V (see Figure 14: "Test circuit for gate charge behavior")	-	147	-	nC
Q_{gs}	Gate-source charge		-	44	-	nC
Q_{gd}	Gate-drain charge		-	46	-	nC

Table 6: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 30\text{ V}$, $I_D = 40\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 13: "Test circuit for resistive load switching times" and Figure 18: "Switching time waveform")	-	40	-	ns
t_r	Rise time		-	71	-	ns
$t_{d(off)}$	Turn-off delay time		-	132	-	ns
t_f	Fall time		-	40	-	ns

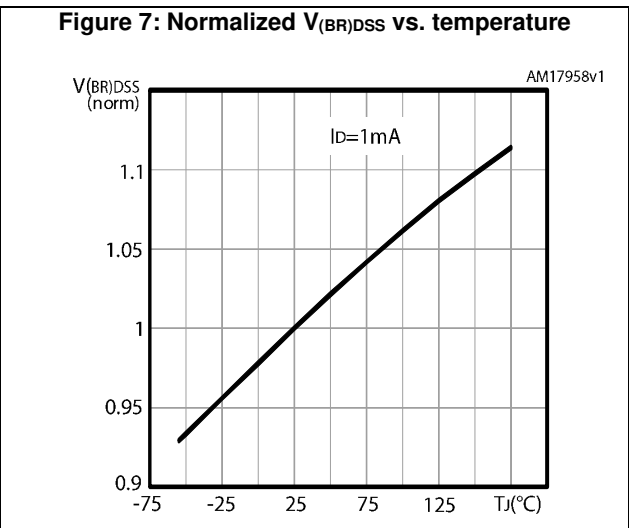
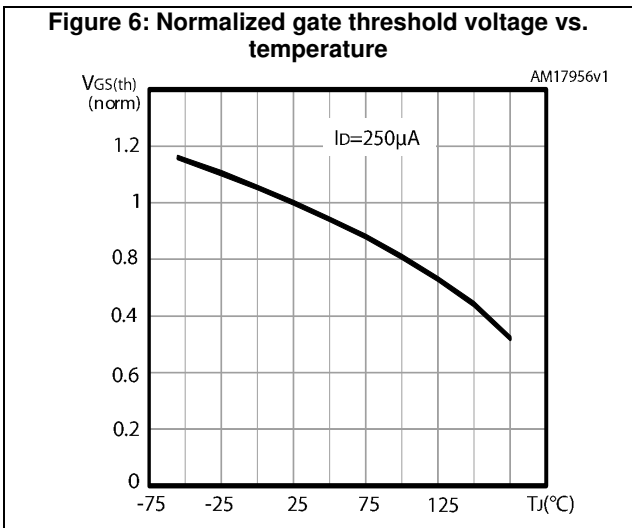
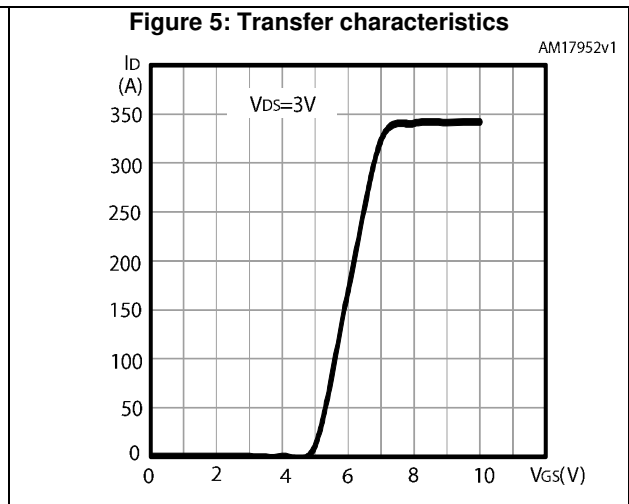
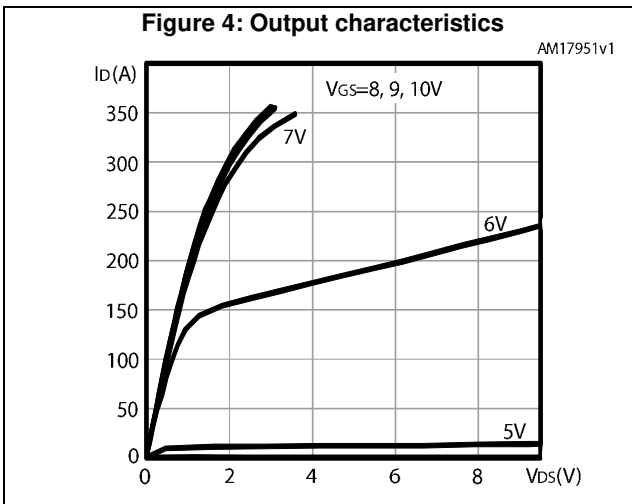
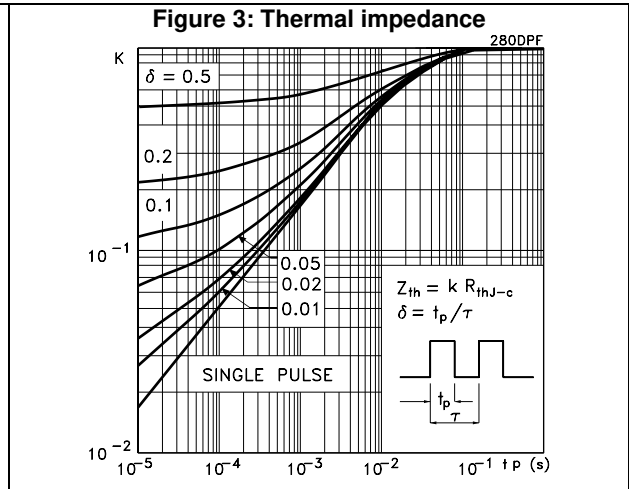
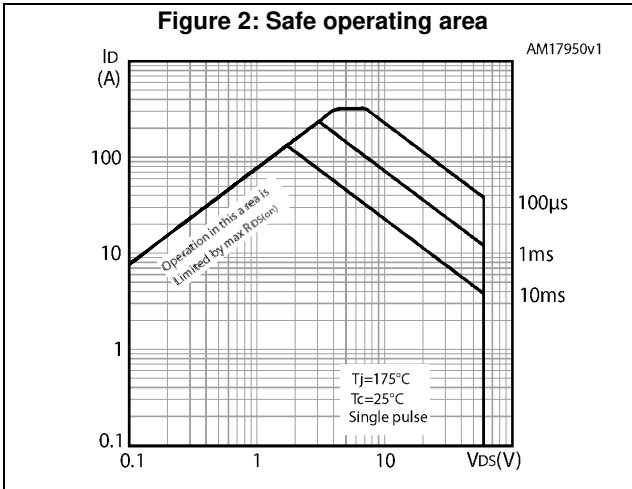
Table 7: Source-drain diode

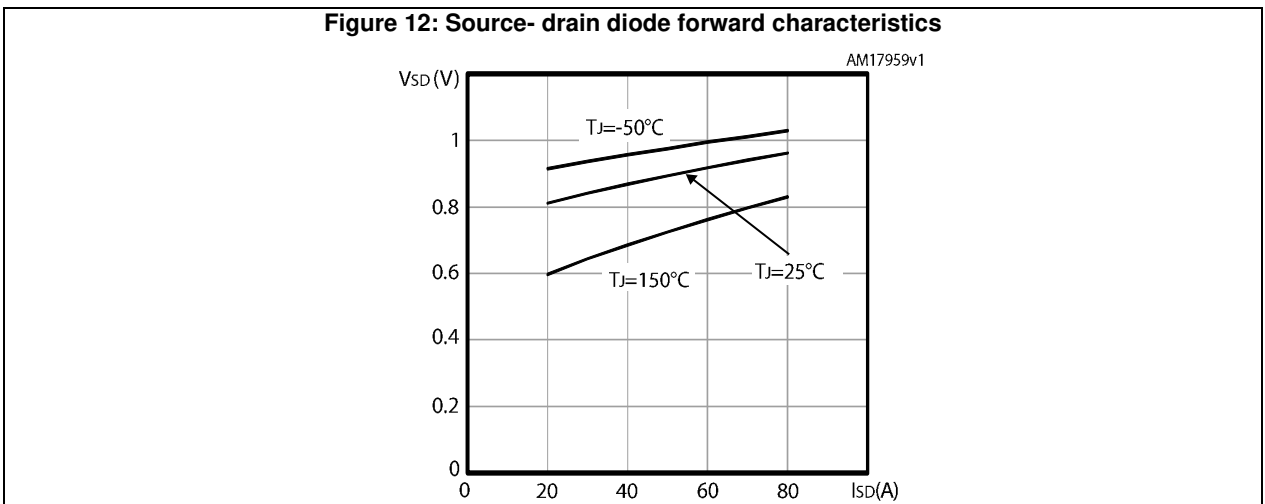
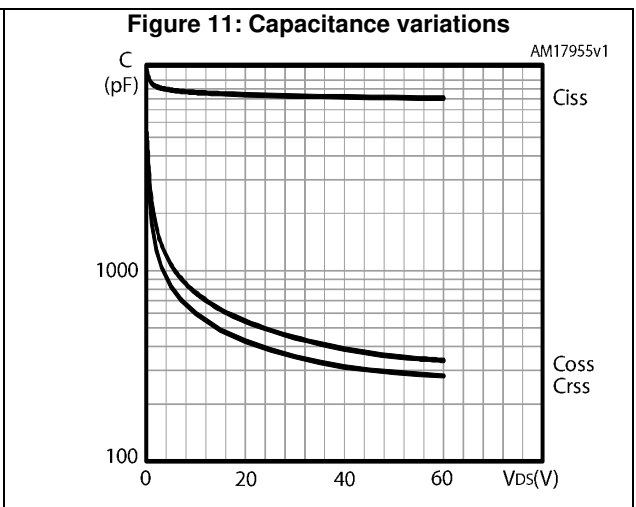
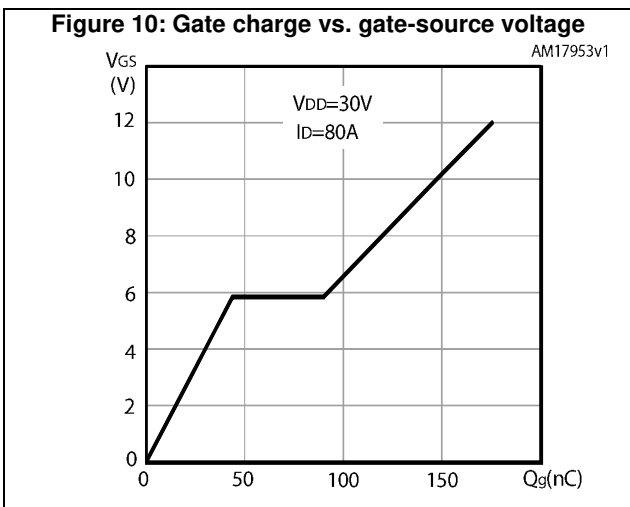
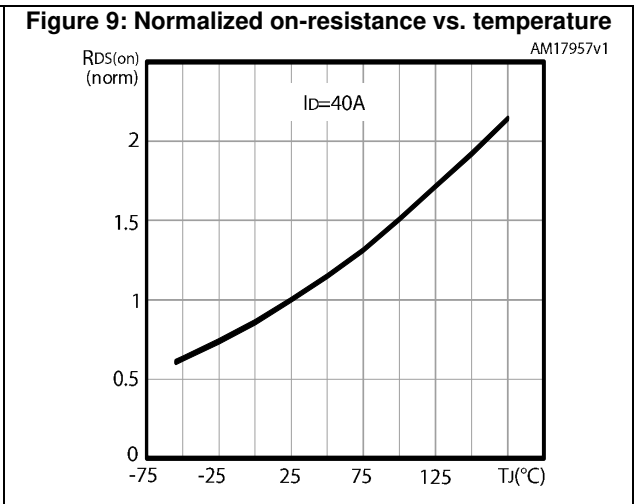
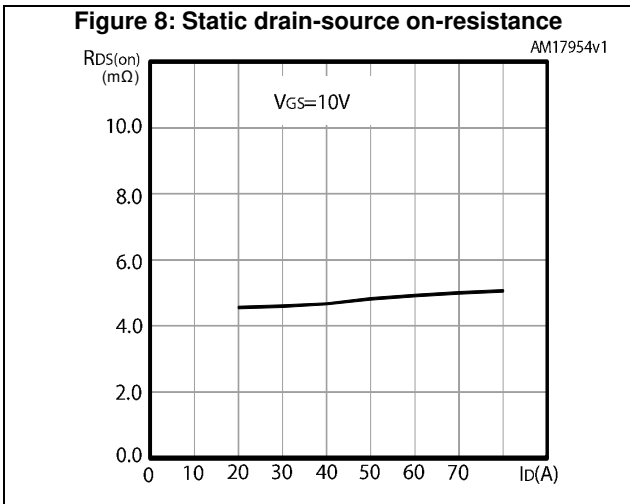
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}^{(1)}$	Source-drain current		-		80	A
$I_{SDM}^{(2)}$	Source-drain current (pulsed)		-		320	A
$V_{SD}^{(3)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 80\text{ A}$	-		1.3	V
t_{rr}	Reverse recovery time	$I_{SD} = 80\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 48\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 15: "Test circuit for inductive load switching and diode recovery times")	-	46		ns
Q_{rr}	Reverse recovery charge		-	65		nC
I_{RRM}	Reverse recovery current		-	2.8		A

Notes:

- (1) Current limited by package.
(2) Pulse width limited by safe operating area.
(3) Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

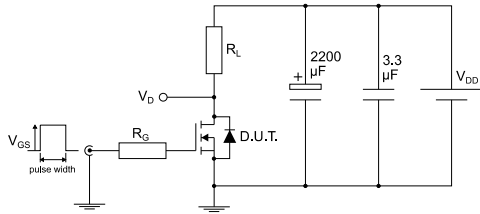
2.1 Electrical characteristics (curves)





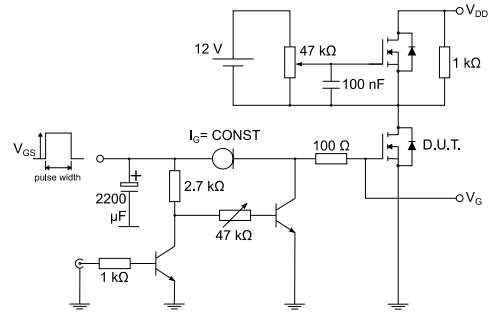
3 Test circuits

Figure 13: Test circuit for resistive load switching times



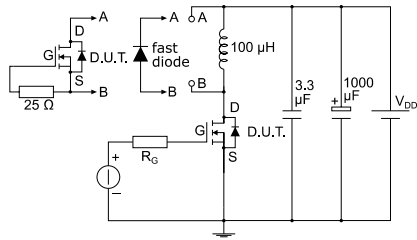
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Figure 14: Test circuit for gate charge behavior



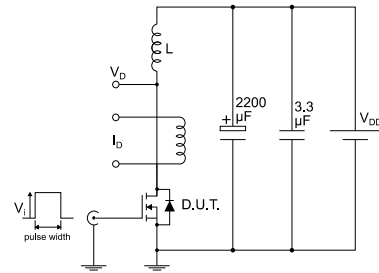
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Figure 15: Test circuit for inductive load switching and diode recovery times



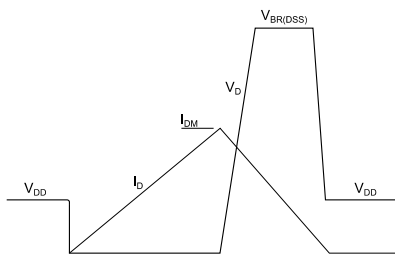
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Figure 16: Unclamped inductive load test circuit



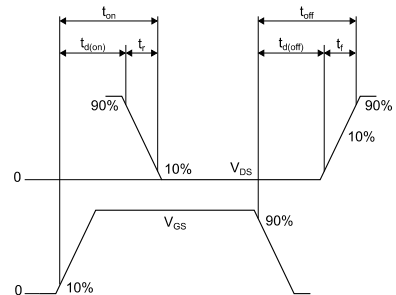
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Figure 17: Unclamped inductive waveform



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Figure 18: Switching time waveform



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4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 DPAK (TO-252) type A2 package information

Figure 19: DPAK (TO-252) type A2 package outline

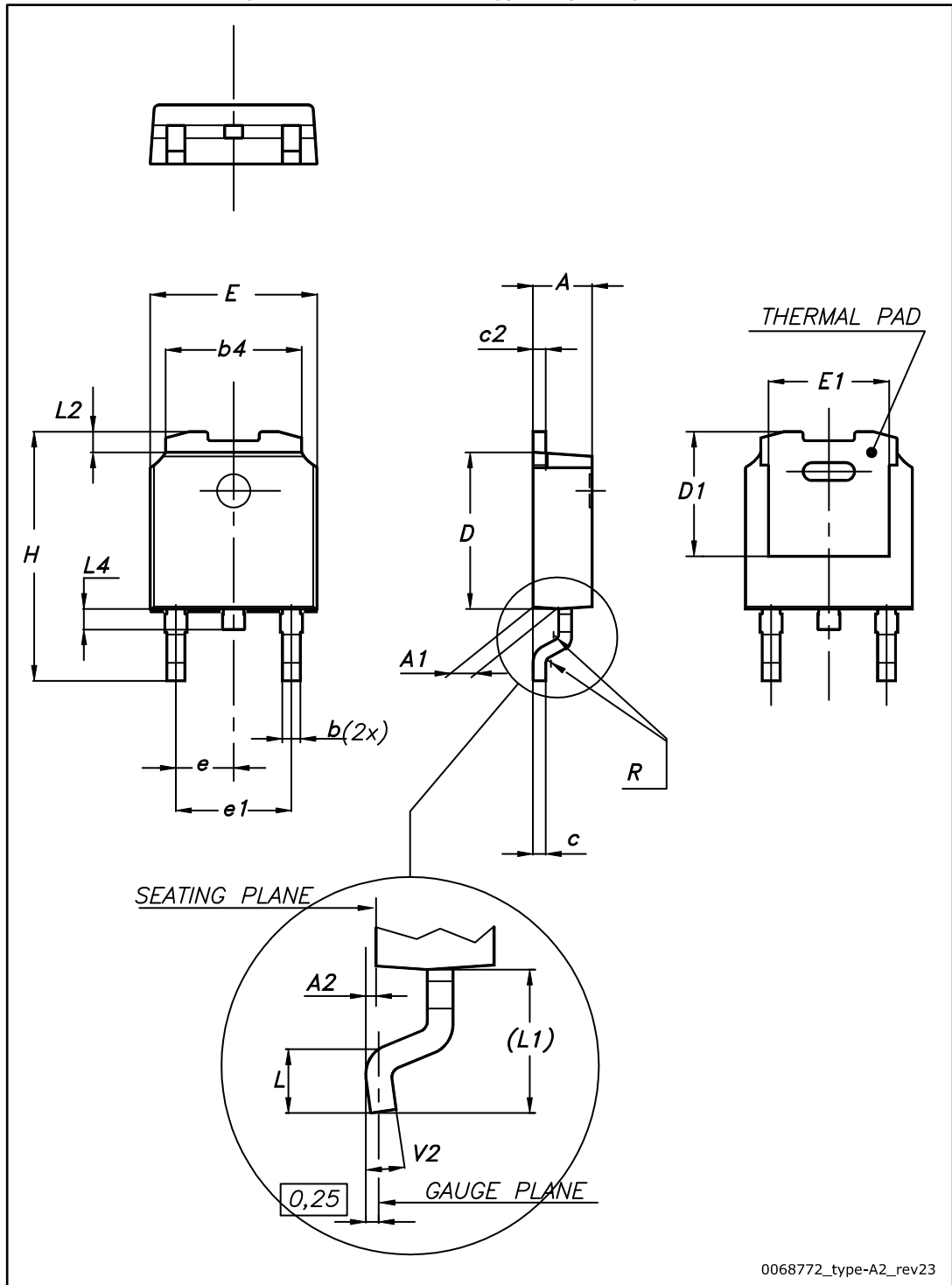
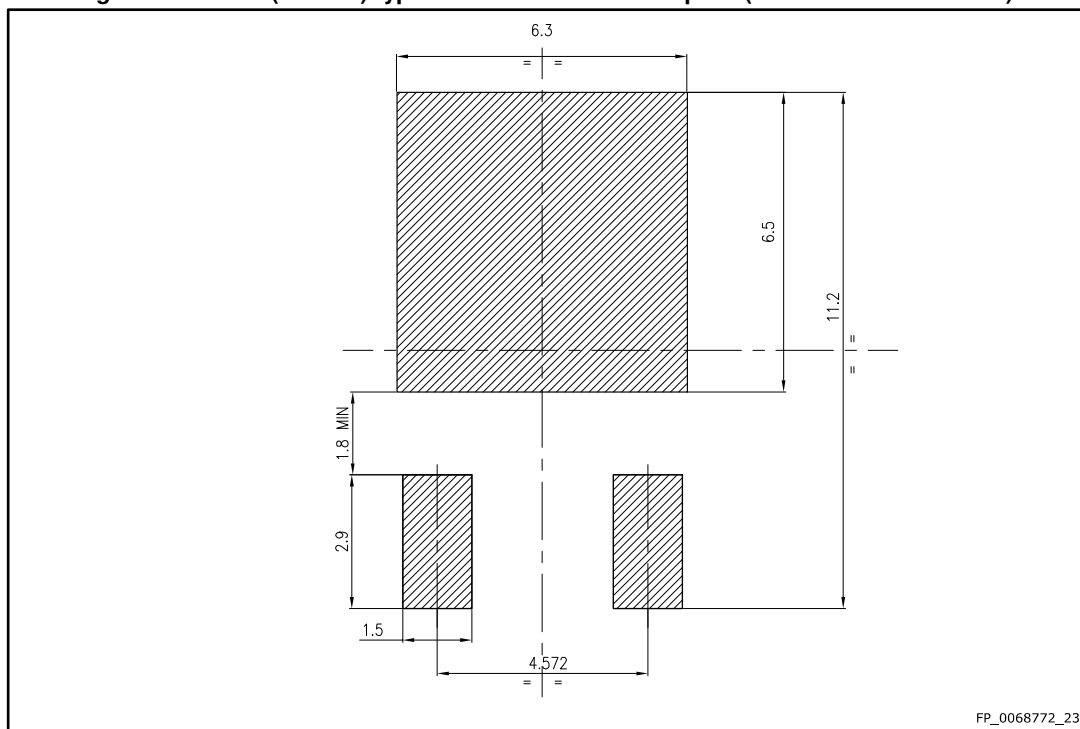


Table 8: DPAK (TO-252) type A2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.16	2.28	2.40
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 20: DPAK (TO-252) type A2 recommended footprint (dimensions are in mm)



4.2 DPAK (TO-252) tape and reel mechanical data

Figure 21: DPAK (TO-252) tape outline

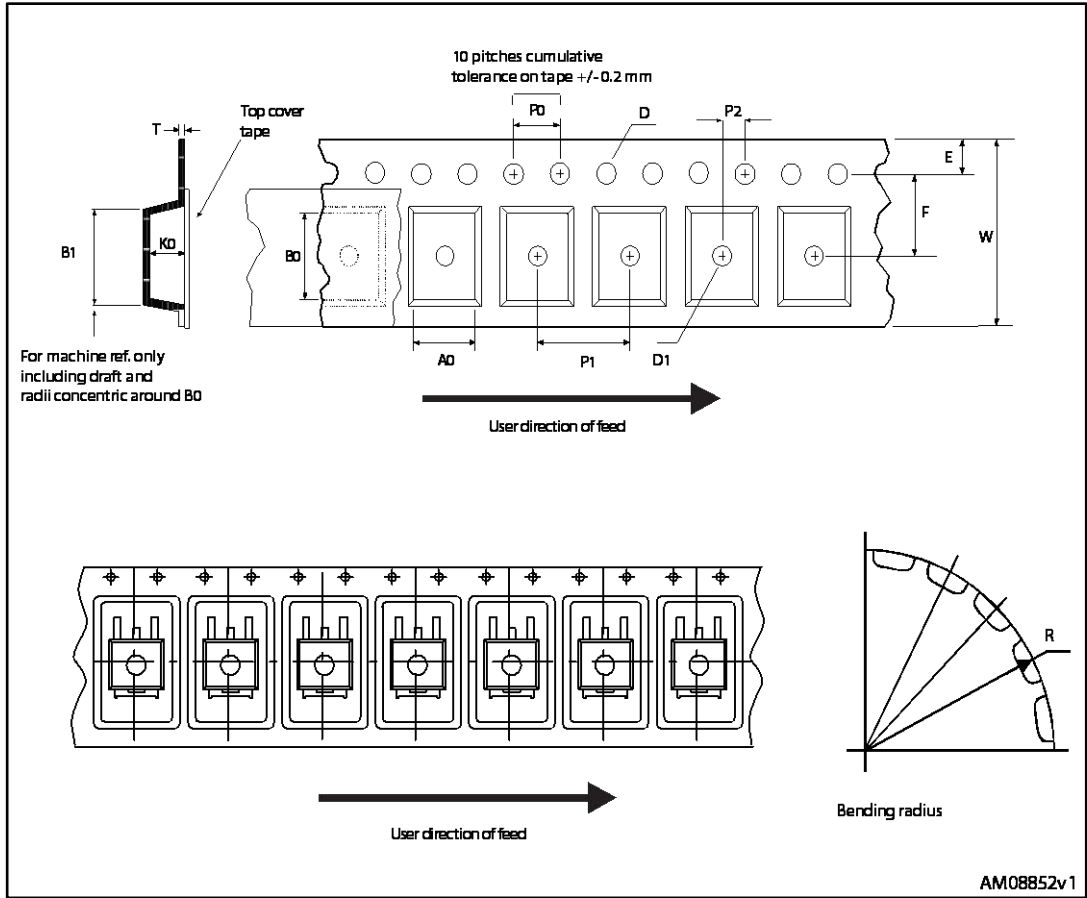


Figure 22: DPAK (TO-252) reel outline

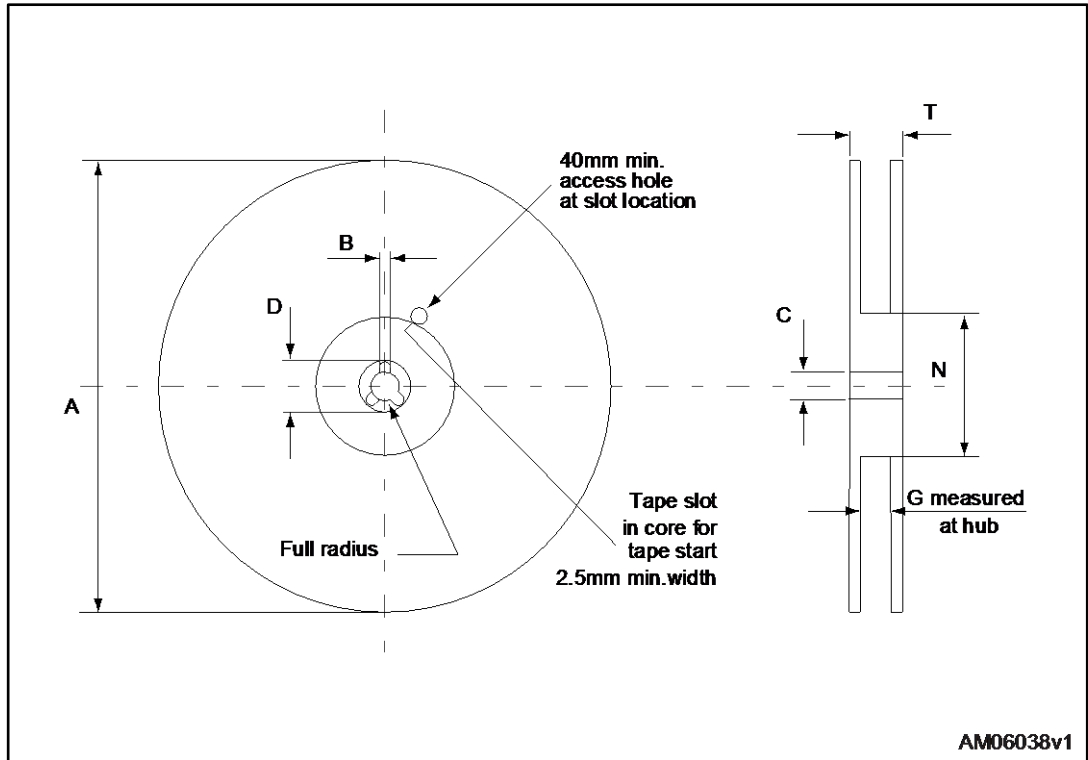


Table 9: DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

5 Revision history

Table 10: Document revision history

Date	Revision	Changes
08-Aug-2012	1	Initial release.
17-Jan-2014	2	<ul style="list-style-type: none"> – Document status promoted from preliminary to production data – Modified: title – Modified: Features – Added: note 1 in cover page – Modified: RDS(on)max and ID values in cover page – Modified: Derating factor value in Table 2 – Modified: RDS(on) values in Table 4 – Modified: ID and the entire typical values in Table 5, 6 and 7 – Added: Section 2.1: Electrical characteristics (curves) – Updated: Section 3: Package mechanical data – Minor text changes
23-May-2017	3	<p>Modified title and features on cover page.</p> <p>Modified Table 3: "Thermal data".</p> <p>Modified Section 4: "Package mechanical data".</p> <p>Minor text changes.</p>

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